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FIG. 1

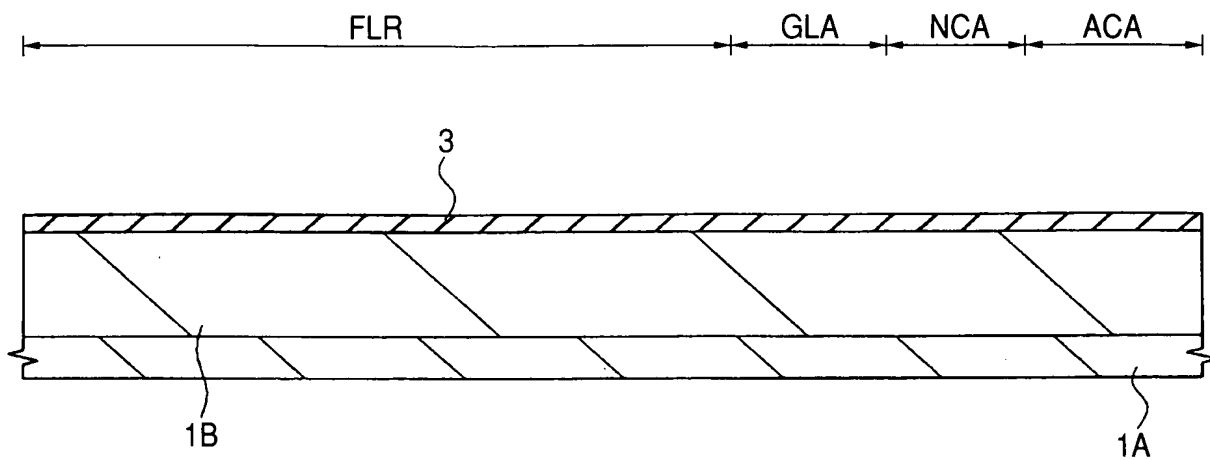
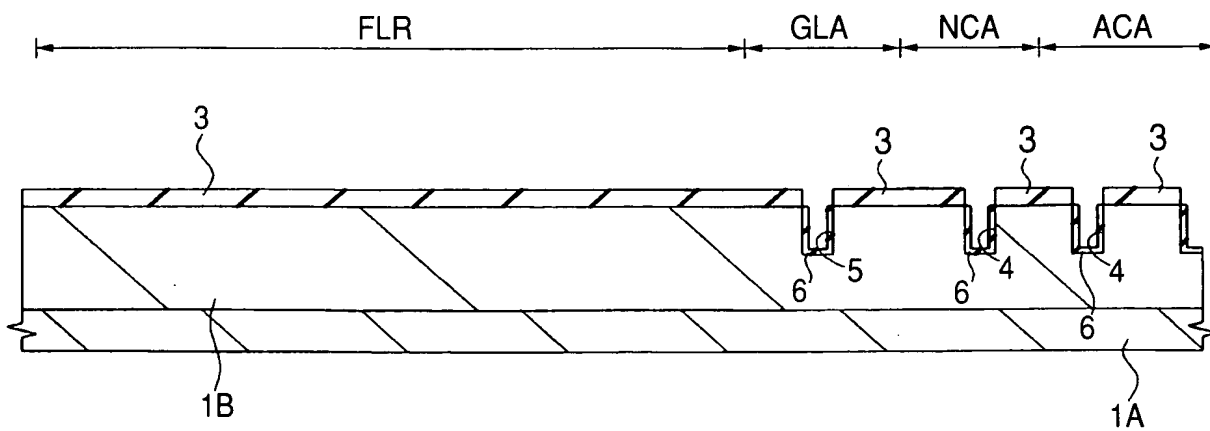


FIG. 2



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FIG. 3

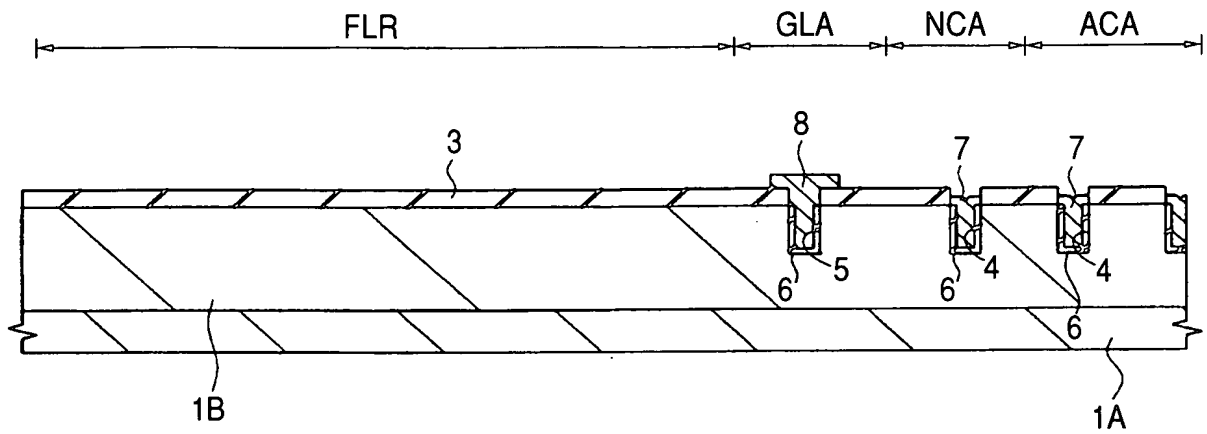
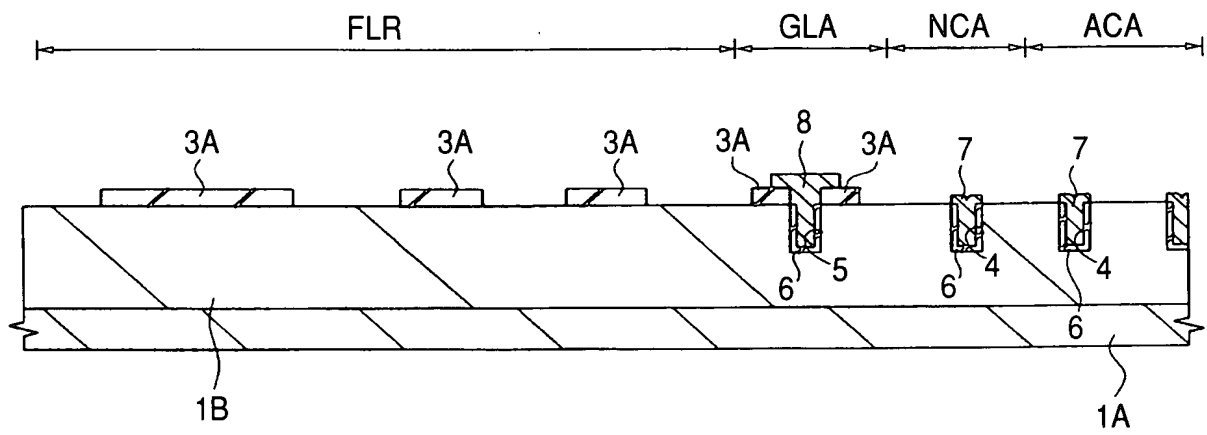


FIG. 4



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FIG. 5

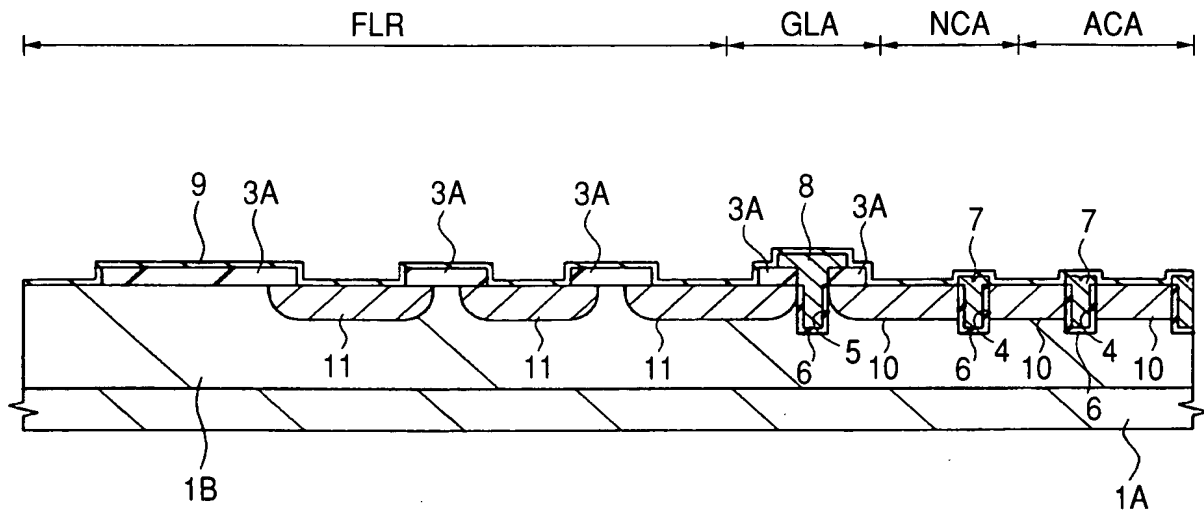
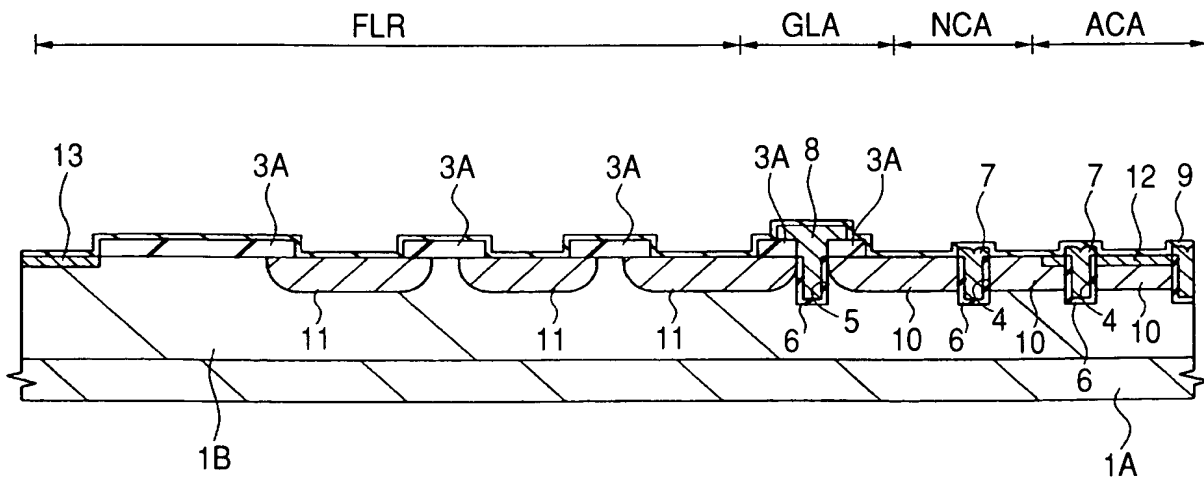


FIG. 6



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FIG. 7

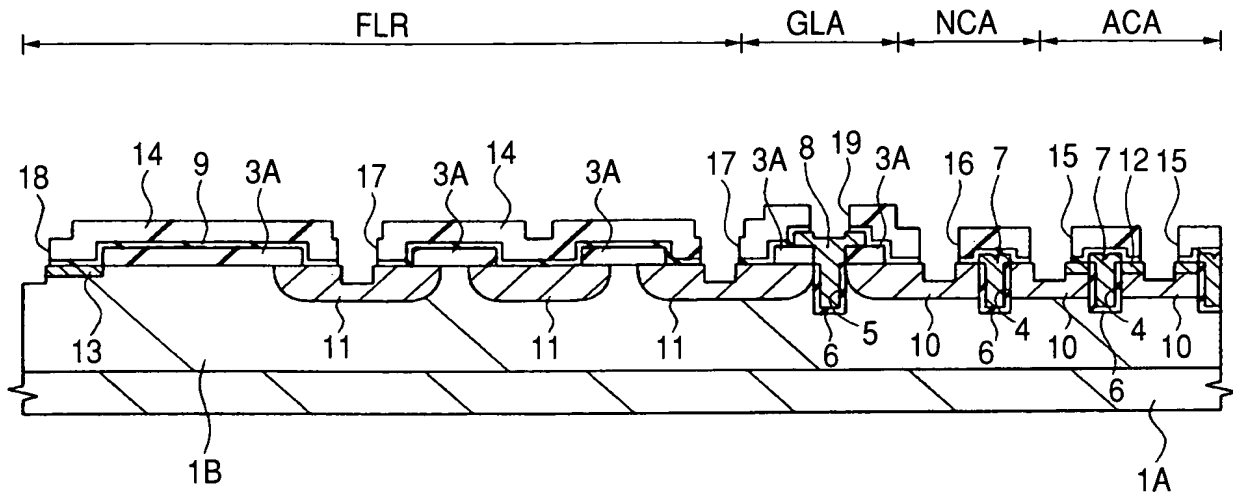
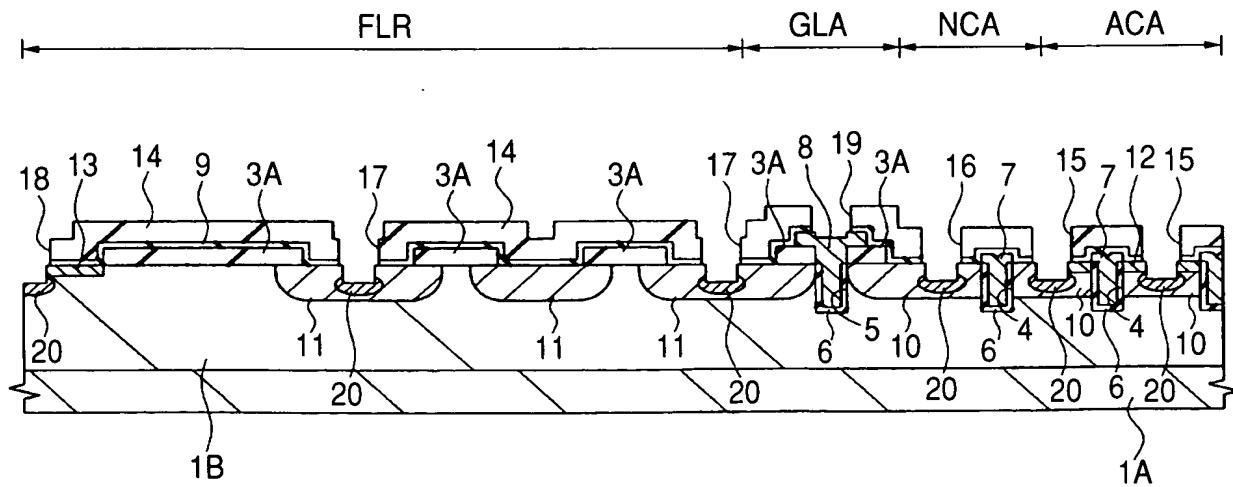
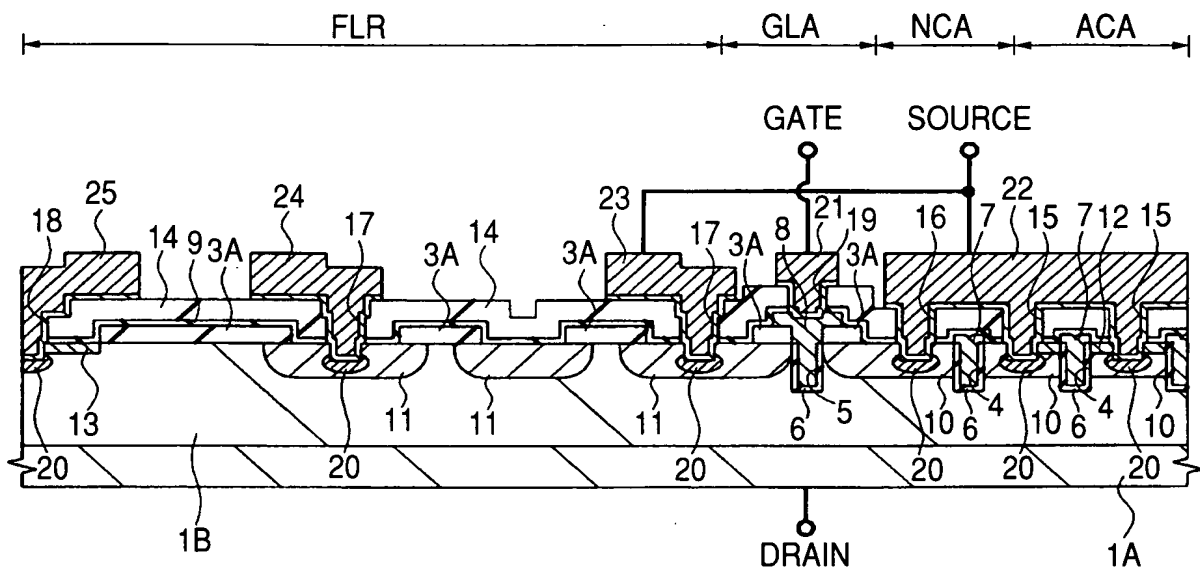


FIG. 8



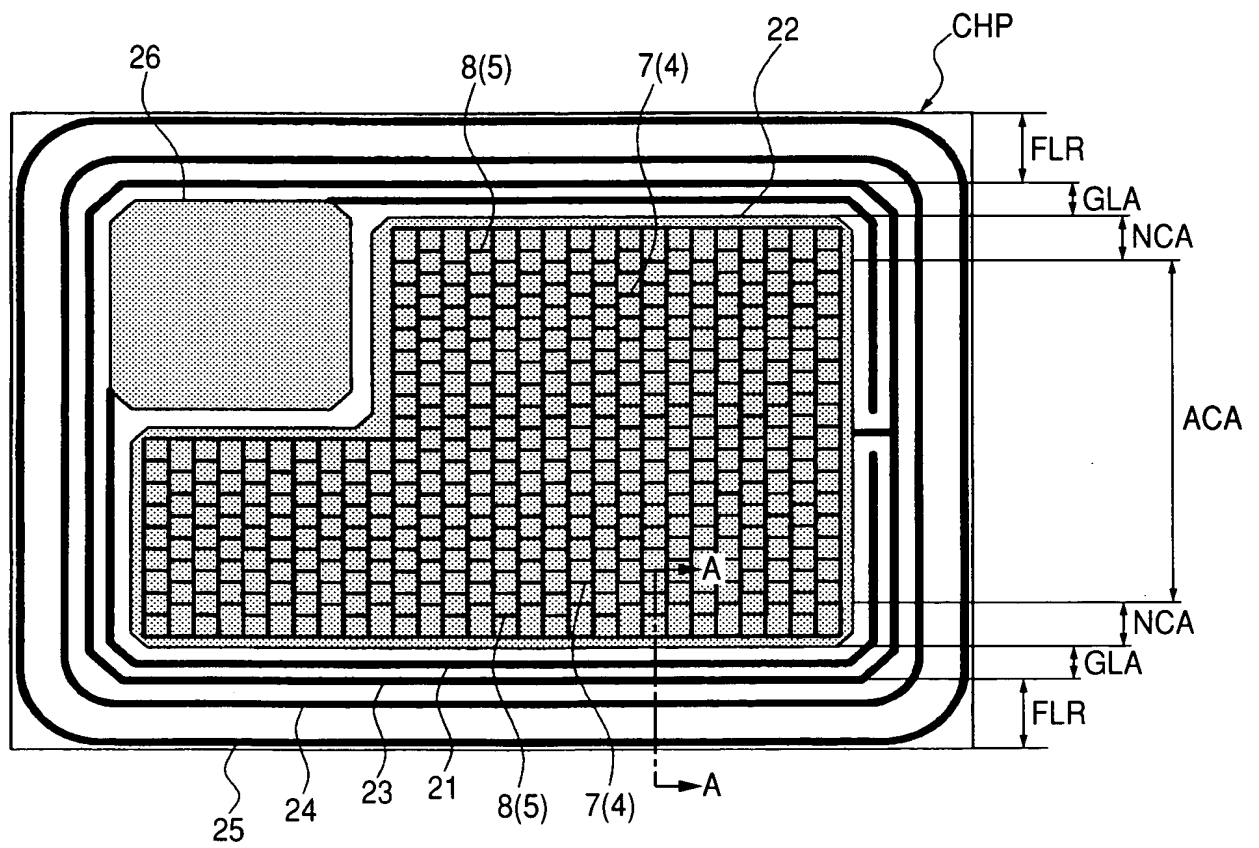
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FIG. 9



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FIG. 10



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FIG. 11

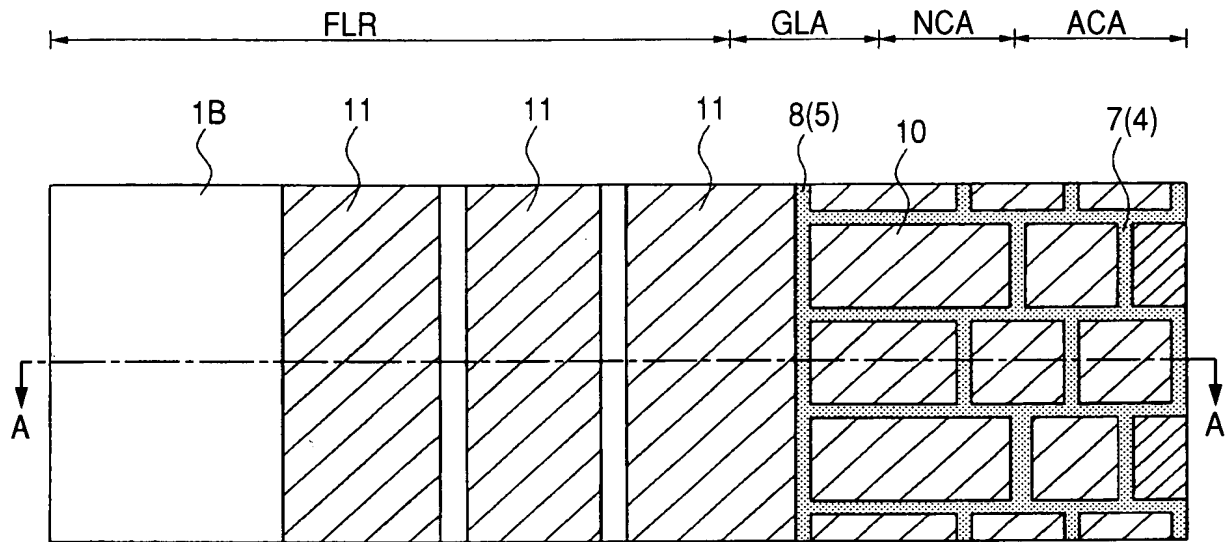
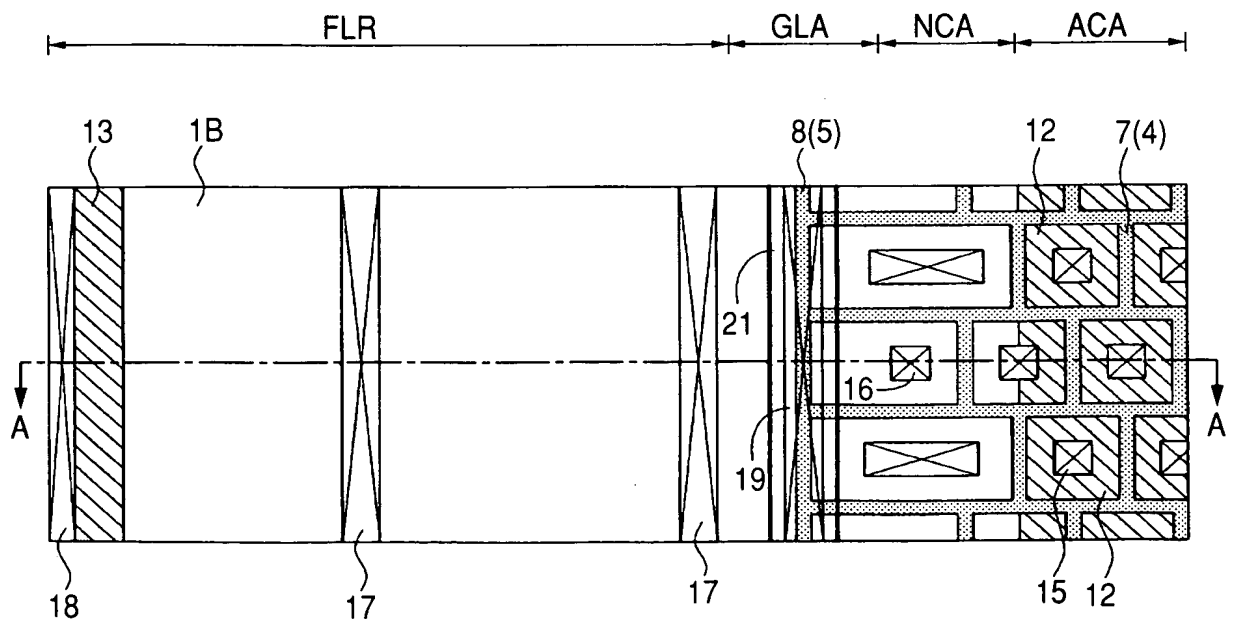
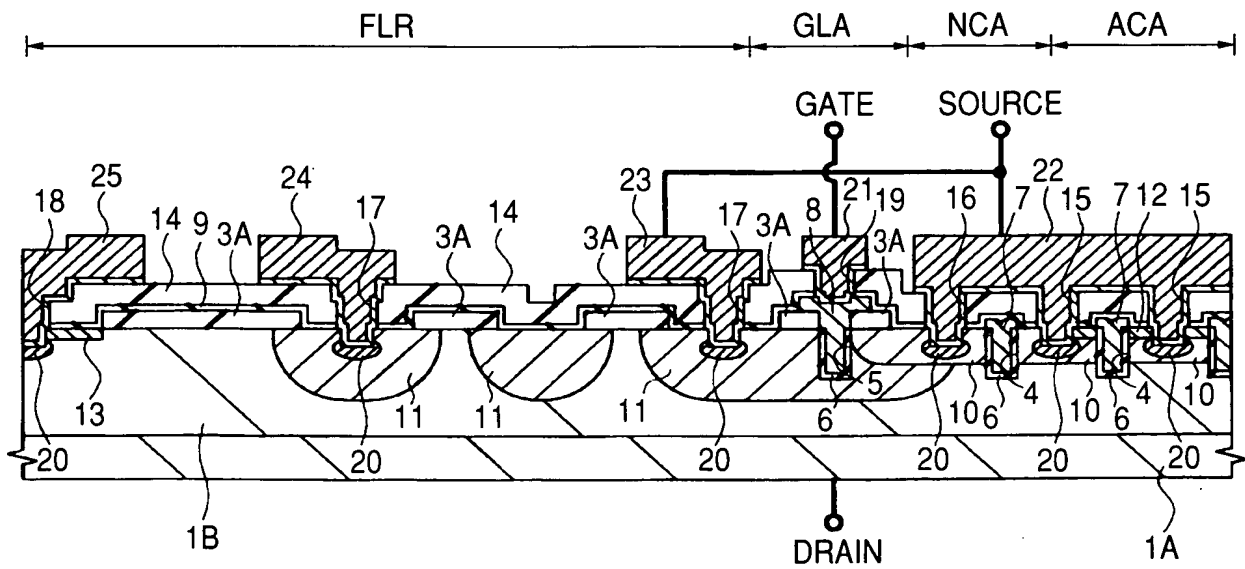


FIG. 12





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FIG. 15

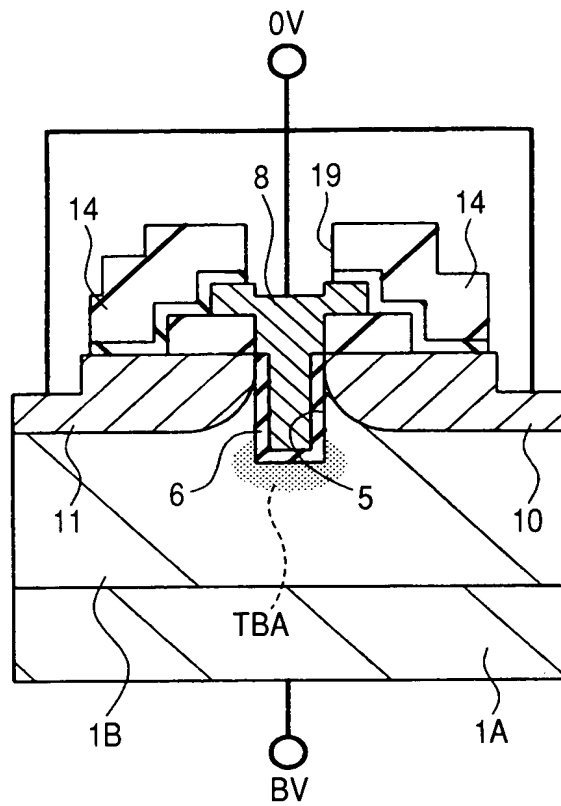
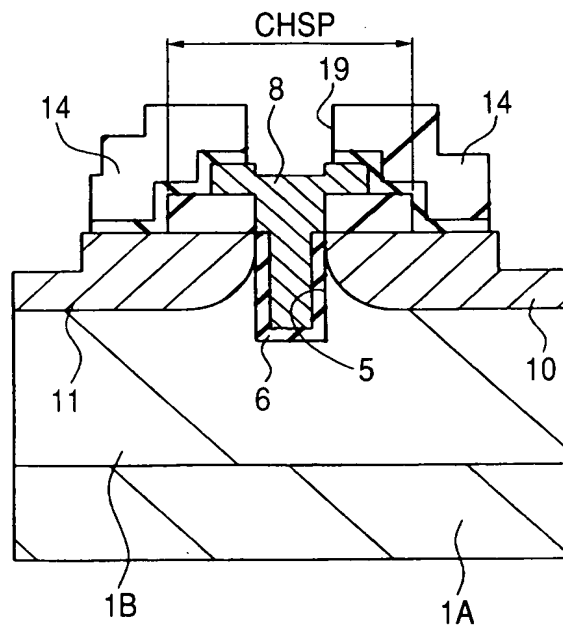


FIG. 16



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FIG. 17

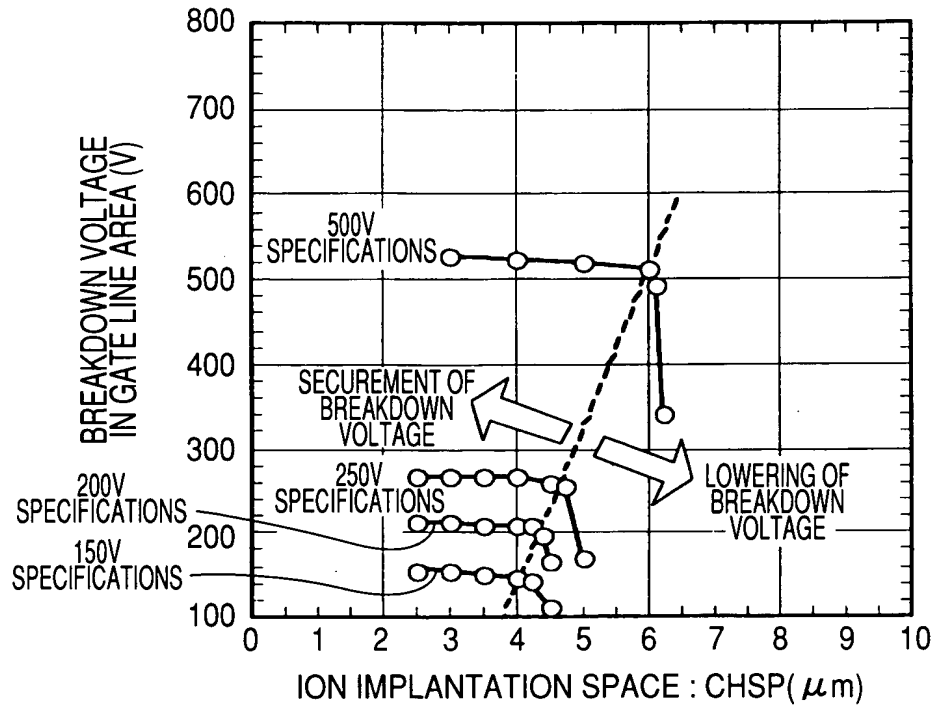
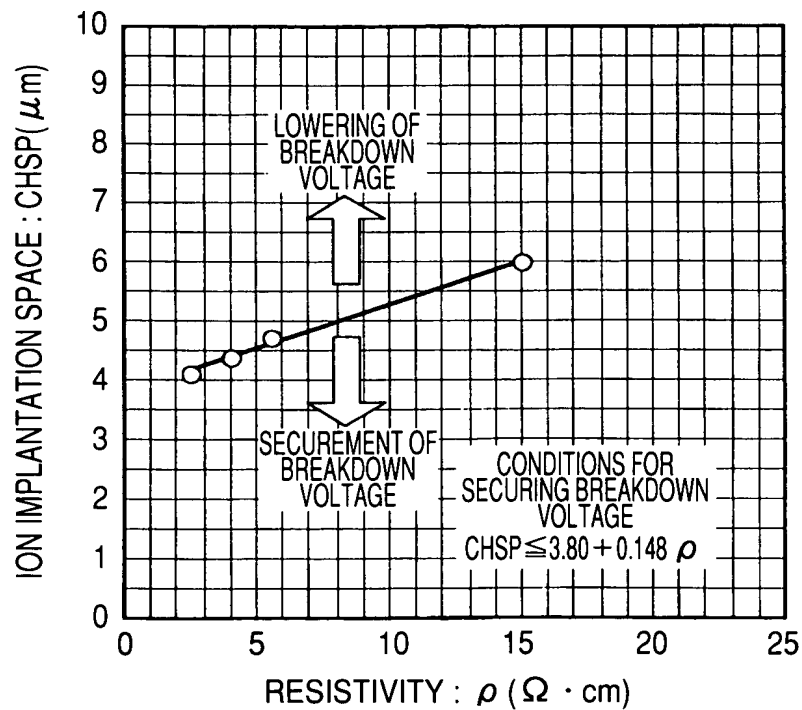


FIG. 18



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FIG. 19

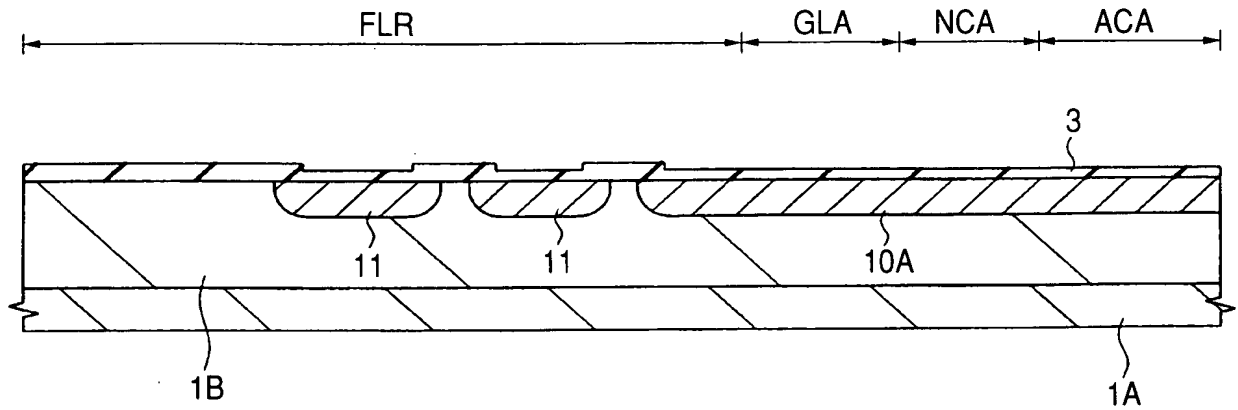
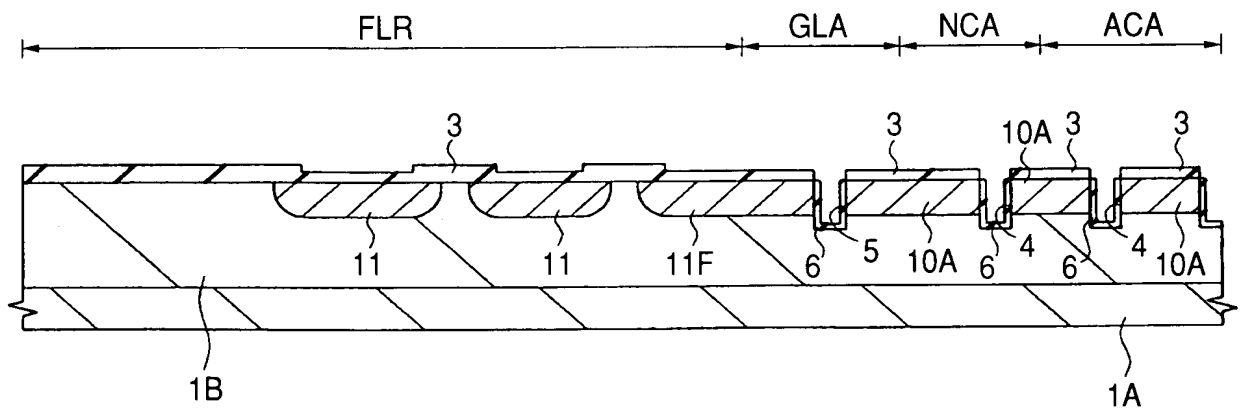


FIG. 20



A cross-sectional view of a polymer film 1. The film has a main body 1A and a bottom layer 1B. A patterned layer 3 is formed on the top surface of the main body 1A. The patterned layer 3 consists of a series of rectangular blocks 3A separated by recessed regions 11. The recessed regions 11 are further divided into regions 11A and 11B. A conductive layer 4 is formed on the top surface of the patterned layer 3. The conductive layer 4 is formed in the recessed regions 11 and in the regions 11A and 11B. The conductive layer 4 is formed in the regions 11A and 11B by a process involving a conductive paste 5 and a conductive paste 6. The conductive layer 4 is formed in the regions 11A and 11B by a process involving a conductive paste 5 and a conductive paste 6. The conductive layer 4 is formed in the regions 11A and 11B by a process involving a conductive paste 5 and a conductive paste 6.

A detailed cross-sectional view of a semiconductor device, likely a CCD or image sensor array. The device is divided into four horizontal regions: FLR (Front Layer Region), GLA (Gate Layer Area), NCA (N-channel Area), and ACA (Anode Contact Area). The structure includes a substrate (1A) with a thin layer (1B) on top. Various layers and contacts are labeled with numbers: 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11, 12, 13, 14, 15, 16, 17, 18, 19, 20, 21, 22, 23, 24, 25. Key features include a GATE electrode connected to a GATE terminal, a SOURCE electrode connected to a SOURCE terminal, and a DRAIN electrode connected to a DRAIN terminal. The device shows a series of gates and contacts, with some regions having a different material composition or doping level, indicated by hatching patterns.

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FIG. 23

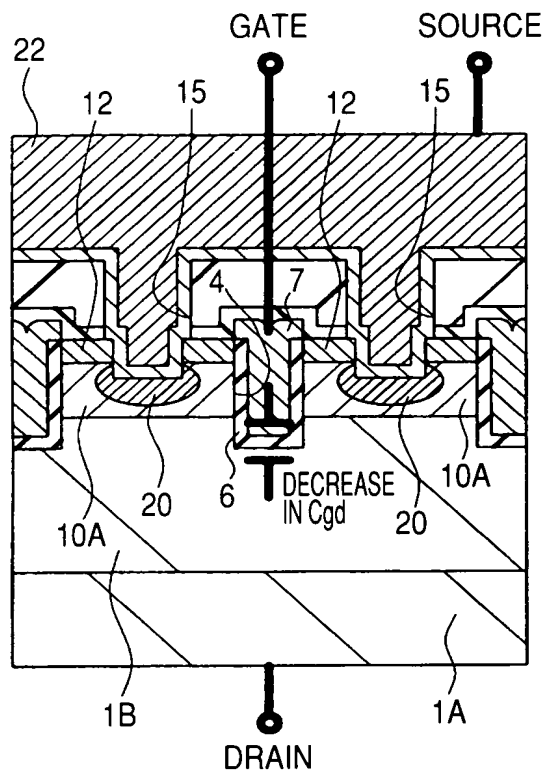
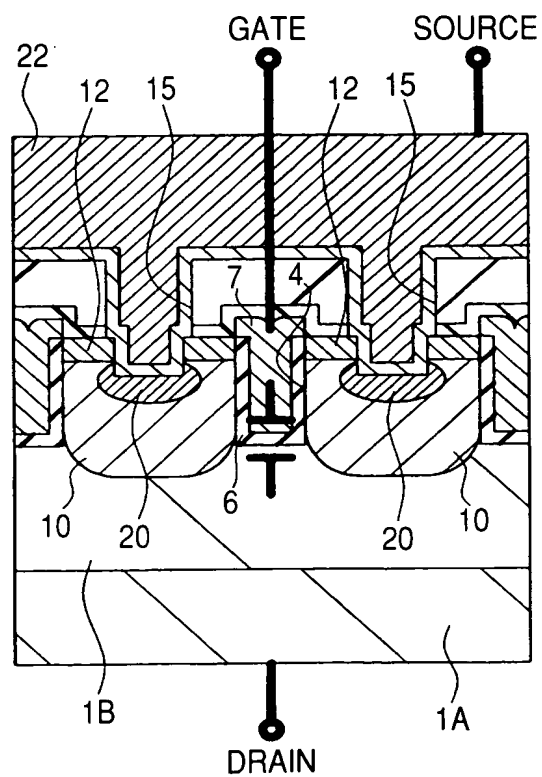


FIG. 24



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FIG. 25

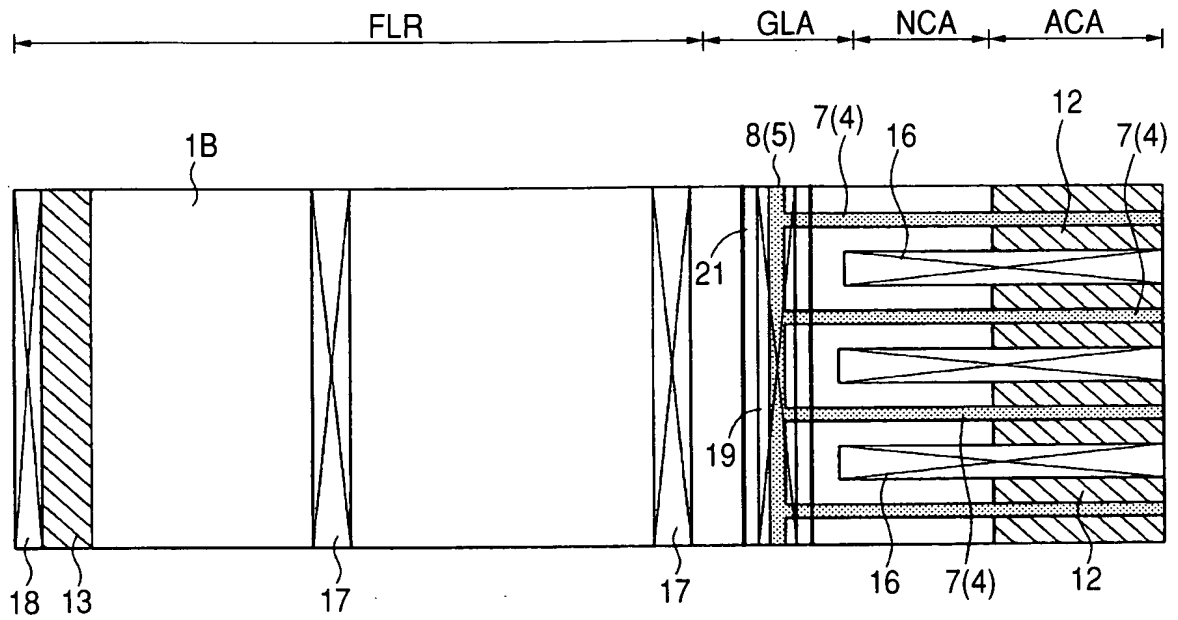
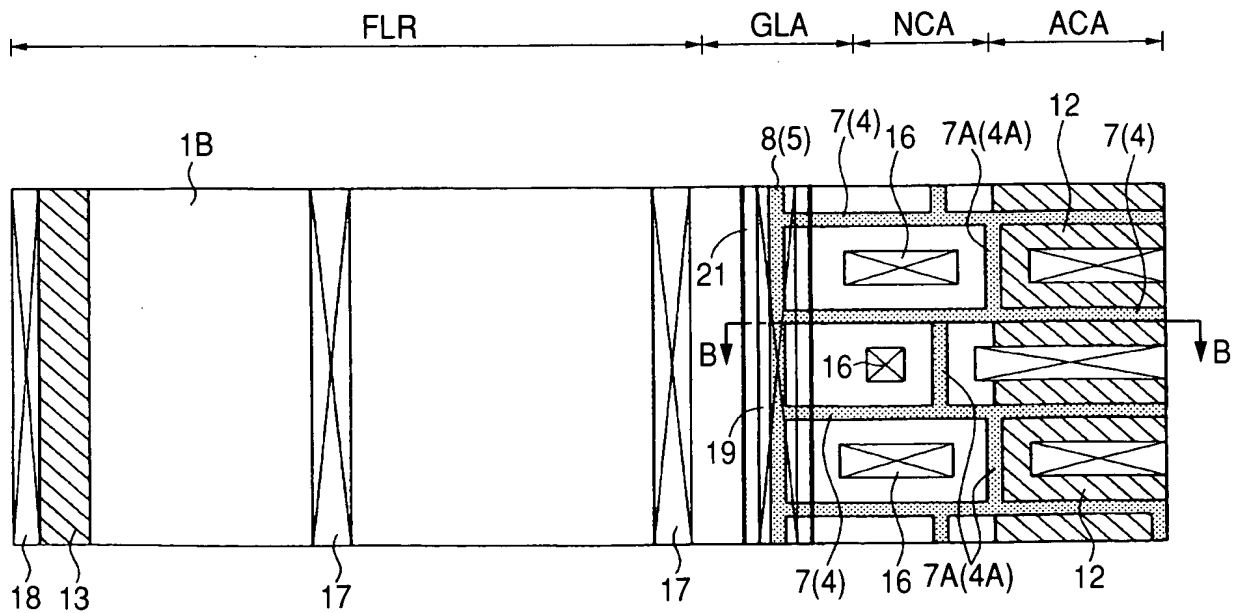


FIG. 26



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FIG. 27

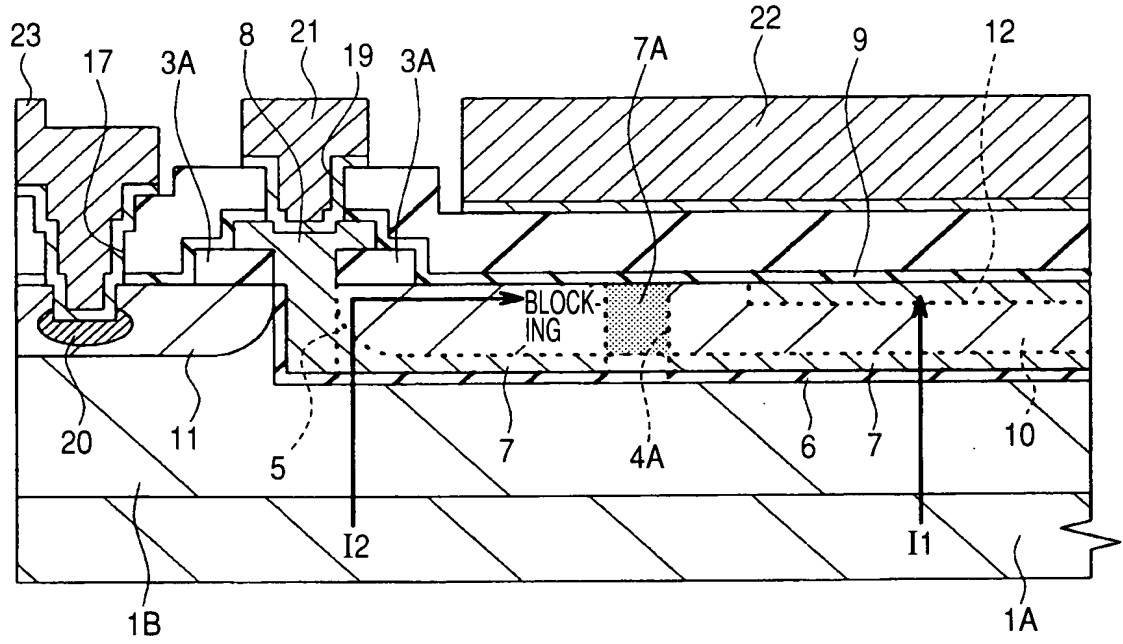


FIG. 28

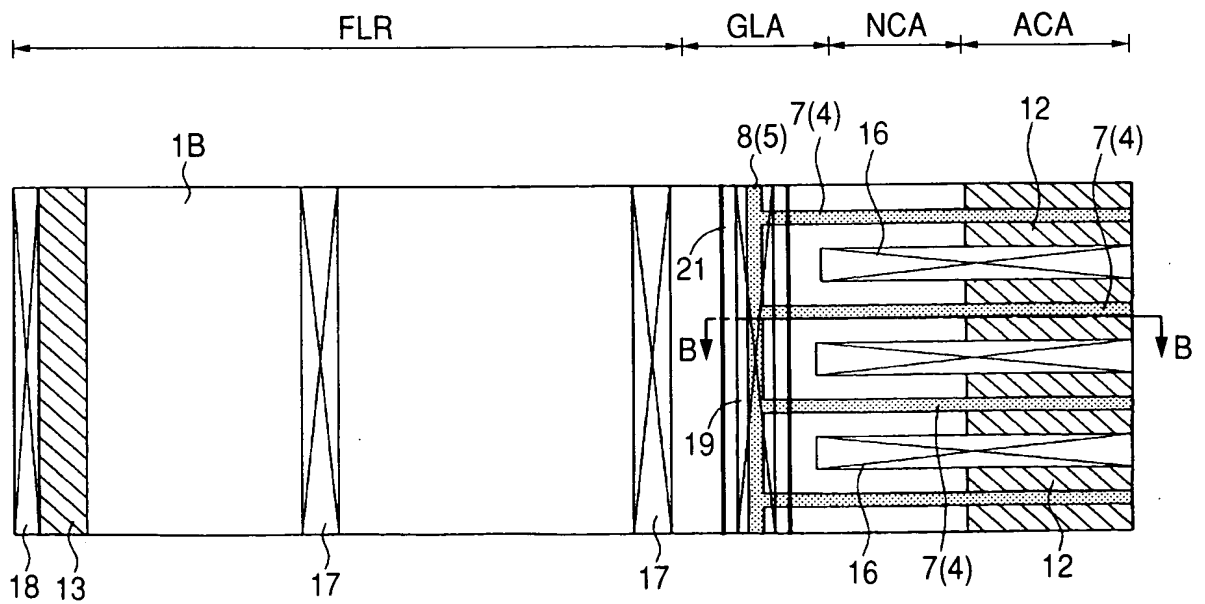


FIG. 29

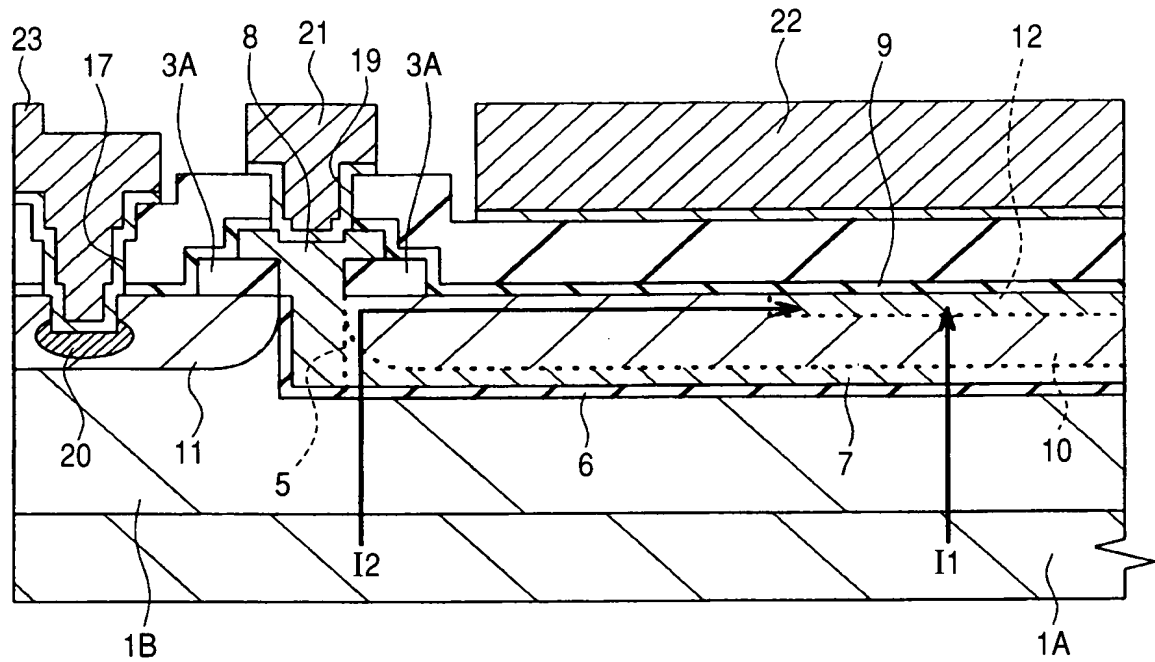
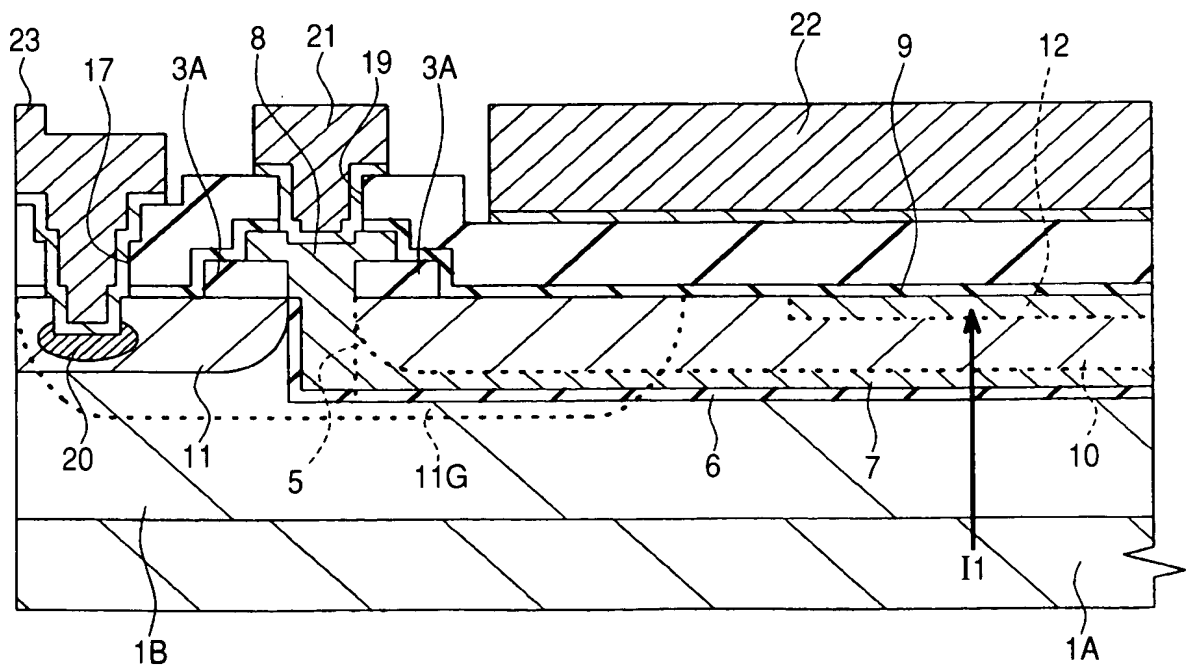


FIG. 30



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FIG. 31

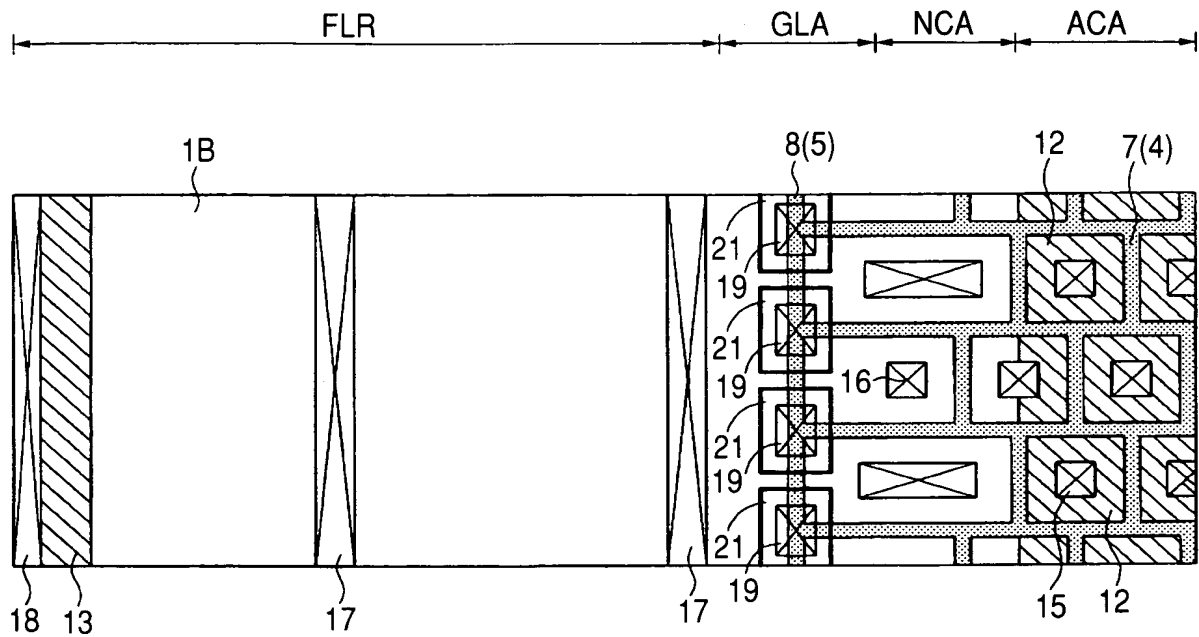


FIG. 32

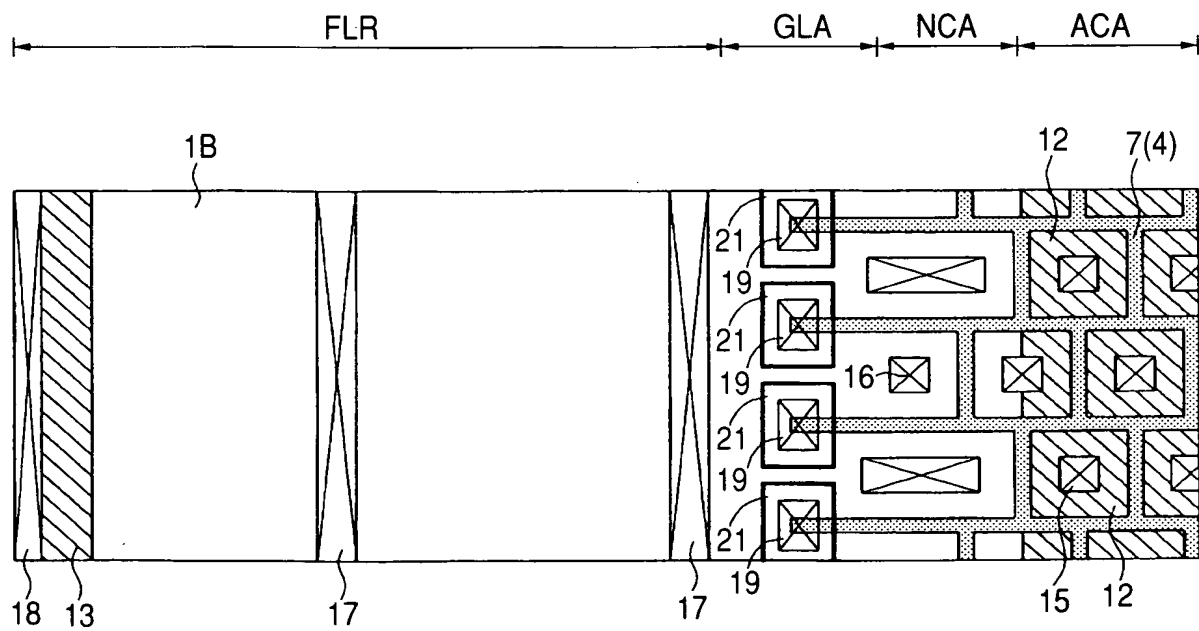


FIG. 33

